

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

\_\_\_\_\_ forming a film to be patterned;  
\_\_\_\_\_ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and  
\_\_\_\_\_ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,

\_\_\_\_\_ wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).

3. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

\_\_\_\_\_ forming a film to be patterned;  
\_\_\_\_\_ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and  
\_\_\_\_\_ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,

\_\_\_\_\_ wherein said top resist pattern is made of a resist material with phenol-based hydroxide.

4. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

forming a film to be patterned;  
forming, on said film, a laminated resist pattern with a T-shaped cross section  
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top  
resist pattern being larger than a surface area of said bottom resist pattern; and  
increasing a width of said top resist pattern after said film is patterned via said  
laminated resist pattern,  
\_\_\_\_\_ wherein said surface area of said top resist pattern is increased by coating a  
water-soluble resin at least over said top resist pattern of said laminated resist pattern.

5. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

6. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

7. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

forming a film to be patterned;  
forming, on said film, a laminated resist pattern with a T-shaped cross section  
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top  
resist pattern being larger than a surface area of said bottom resist pattern; and  
increasing a width of said top resist pattern after said film is patterned via said  
laminated resist pattern,  
\_\_\_\_\_ wherein said laminated resist pattern is not removed through the fabrication  
process of patterned thin film.

8. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

\_\_\_\_\_ forming a film to be patterned;  
\_\_\_\_\_ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and  
\_\_\_\_\_ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,  
\_\_\_\_\_ wherein said film is patterned via said laminated resist pattern by means of dry etching.

9. (Canceled)

10. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

\_\_\_\_\_ forming a first thin film to be patterned;  
\_\_\_\_\_ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;  
\_\_\_\_\_ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;  
\_\_\_\_\_ increasing a width of said top resist pattern; and  
\_\_\_\_\_ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,  
\_\_\_\_\_ wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).

11. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

forming a first thin film to be patterned;  
forming, on said first thin film, a laminated resist pattern with a T-shaped  
cross section and composed of a bottom resist pattern and a top resist pattern, a surface area  
of said top resist pattern being larger than a surface area of said bottom resist pattern;  
patterning said first thin film via said laminated resist pattern, to form a first  
patterned thin film;  
increasing a width of said top resist pattern; and  
forming a second patterned thin film along a contour of said top resist pattern  
of said laminated resist pattern,  
\_\_\_\_\_ wherein said top resist pattern is made of a resist material with phenol-based  
hydroxide.

12. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method  
for fabricating a patterned thin film, comprising:

\_\_\_\_\_ forming a first thin film to be patterned;  
\_\_\_\_\_ forming, on said first thin film, a laminated resist pattern with a T-shaped  
cross section and composed of a bottom resist pattern and a top resist pattern, a surface area  
of said top resist pattern being larger than a surface area of said bottom resist pattern;  
\_\_\_\_\_ patterning said first thin film via said laminated resist pattern, to form a first  
patterned thin film;  
\_\_\_\_\_ increasing a width of said top resist pattern; and  
\_\_\_\_\_ forming a second patterned thin film along a contour of said top resist pattern  
of said laminated resist pattern,  
\_\_\_\_\_ wherein said surface area of said top resist pattern is increased by coating a  
water-soluble resin at least over said top resist pattern of said laminated resist pattern.

13. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

14. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

15. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

\_\_\_\_\_ forming a first thin film to be patterned;

\_\_\_\_\_ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

\_\_\_\_\_ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

\_\_\_\_\_ increasing a width of said top resist pattern; and

\_\_\_\_\_ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

\_\_\_\_\_ wherein said laminated resist pattern is not removed through the fabrication process of said first patterned thin film and said second patterned thin film.

16. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

\_\_\_\_\_ forming a first thin film to be patterned;

\_\_\_\_\_ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

\_\_\_\_\_ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

\_\_\_\_\_ increasing a width of said top resist pattern; and

\_\_\_\_\_ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

\_\_\_\_\_ wherein said film is patterned via said laminated resist pattern by means of dry etching.

17. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

\_\_\_\_\_ forming a first thin film to be patterned;

\_\_\_\_\_ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

\_\_\_\_\_ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

\_\_\_\_\_ increasing a width of said top resist pattern; and

\_\_\_\_\_ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

\_\_\_\_\_ wherein said second patterned thin film is located away from said first patterned thin film by a minute gap.

18. (Original) The fabricating method as defined in claim 17, wherein said second patterned thin film is composed of a pair of patterned thin films, which are located at both sides of said first patterned thin film by minute gaps.

19-22. (Canceled)